

	SRAM	DRAM	NAND Flash	PCRAM	MRAM (STT-RAM)
Data Retention	N	N	Y	Y	Y
Memory Cell Factor (F ²)	50-120	6-10	2-5	6-12	4-20
Read Time (ns)	1	30	50	20-50	2-20
Write /Erase Time (ns)	1	50	106-10 ⁵	50-120	2-20
Number of Rewrites	10 ¹⁶	10 ¹⁶	10 ⁵	10 ¹⁰	10 ¹⁵
Power Read/Write	Low	Low	High	Low	Low
Power (Other than R/W)	Leakage Current	Refresh Power	None	None	None